



# **Fast Recovery Diode**

Replaces March 1998 version, DS4211-2.2

DS4211-3.0 January 2000

**KEY PARAMETERS** 

#### **APPLICATIONS**

- Induction Heating
- A.C. Motor Drives
- Snubber Diode
- Welding
- High Frequency Rectification
- **■** UPS

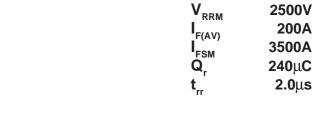
### **FEATURES**

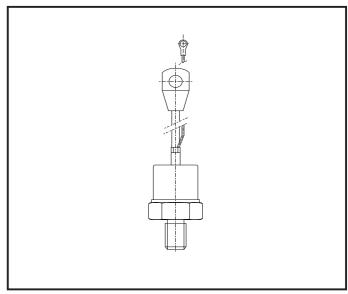
- Thermal Fatigue Free Pressure Contact
- High Surge Capability
- Low Recovery Charge

### **VOLTAGE RATINGS**

Type Number	Repetitive Peak Reverse Voltage V	Conditions
TV18 25F M or K TV18 24F M or K TV18 22F M or K TV18 20F M or K	2500 2400 2200 2000	$V_{RSM} = V_{RRM} + 100V$

For 3/4" 16 UNF thread, add suffix K, e.g. TV18 25FK. For M16 thread, add suffix M, e.g. TV18 25FM. For stud anode add 'R' to type number, e.g. TV18 25FMR.





Outline type codes: DO9. See Package Details for further information.

#### **CURRENT RATINGS**

Symbol	Parameter	Conditions	Max.	Units
I <sub>F(AV)</sub>	Mean forward current	Half wave resistive load, T <sub>case</sub> = 65°C	200	А
I <sub>F(RMS)</sub>	RMS value	$T_{case} = 65^{\circ}C$	320	А

# TV18..F

# **SURGE RATINGS**

Symbol	Parameter	Conditions	Max.	Units
I <sub>FSM</sub>	Surge (non-repetitive) forward current	40mm half aine with 00/ \/ T 45000	3.5	kA
l <sup>2</sup> t	I <sup>2</sup> t for fusing	10ms half sine; with 0% $V_{RRM}$ , $T_j = 150$ °C	61 x 10 <sup>3</sup>	A <sup>2</sup> s
I <sub>FSM</sub>	Surge (non-repetitive) forward current	10mg half ging; with 50% V T = 150°C	2.8	kA
l <sup>2</sup> t	I <sup>2</sup> t for fusing	10ms half sine; with 50% $V_{RRM}$ , $T_j = 150$ °C	39.2x 10 <sup>3</sup>	A²s

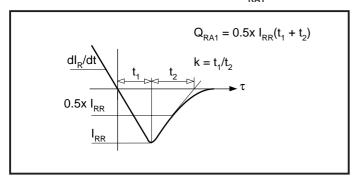
## THERMAL AND MECHANICAL DATA

Symbol	Parameter	Conditions	Min.	Max.	Units
R <sub>th(j-c)</sub>	Thermal resistance - junction to case	dc	-	0.16	°C/W
R <sub>th(c-h)</sub>	Thermal resistance - case to heatsink	Mounting torque 35.0Nm with mounting compound	-	0.06	°C/W
T <sub>vj</sub>	Virtual junction temperature	On-state (conducting)	-	150	°C
T <sub>stg</sub>	Storage temperature range		-55	175	°C
-	Mounting torque		30.0	35.0	Nm

### **CHARACTERISTICS**

Symbol	Parameter	Conditions	Тур.	Max.	Units
$V_{\scriptscriptstyle{\sf FM}}$	Forward voltage	At 1000A peak, T <sub>case</sub> = 25°C	-	3.1	V
I <sub>RRM</sub>	Peak reverse current	At V <sub>RRM</sub> , T <sub>case</sub> = 150°C	-	50	mA
t <sub>rr</sub>	Reverse recovery time		-	3.2	μs
Q <sub>RA1</sub>	Recovered charge (50% chord)	$I_F = 1000A$ , $di_{RR}/dt = 100A/\mu s$	-	240	μС
I <sub>RM</sub>	Reverse recovery current	$T_{case} = 150^{\circ}C, V_{R} = 100V$	-	160	А
K	Soft factor		1.3	-	-
$V_{TO}$	Threshold voltage	At T <sub>vj</sub> = 150°C	-	1.64	V
r <sub>T</sub>	Slope resistance	At T <sub>vj</sub> = 150°C	-	1.54	mΩ
$V_{FRM}$	Forward recovery voltage	di/dt = 1000A/ $\mu$ s, T <sub>j</sub> = 125°C	-	120	V

# DEFINITION OF K FACTOR AND $\boldsymbol{Q}_{\text{RA1}}$



### **CURVES**

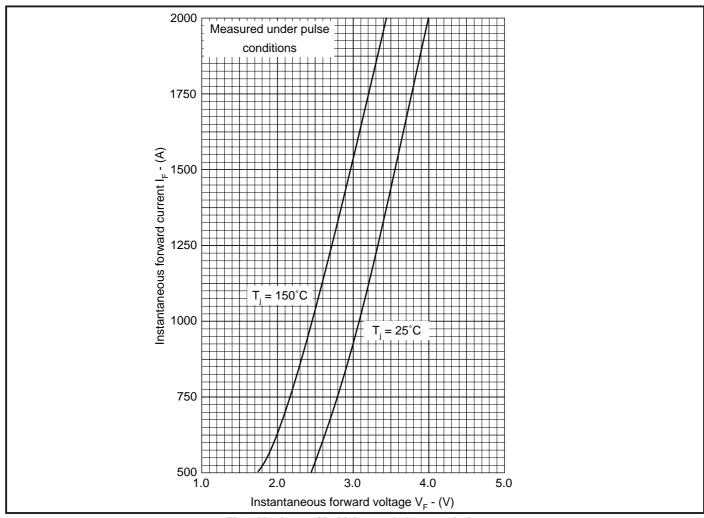


Fig.1 Maximum (limit) forward characteristics

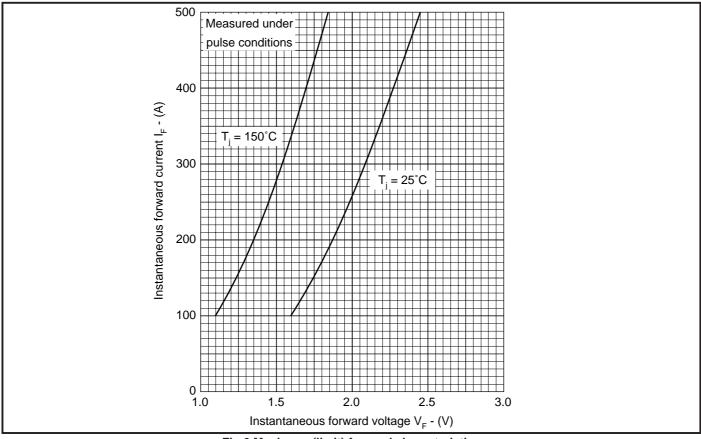


Fig.2 Maximum (limit) forward characteristics

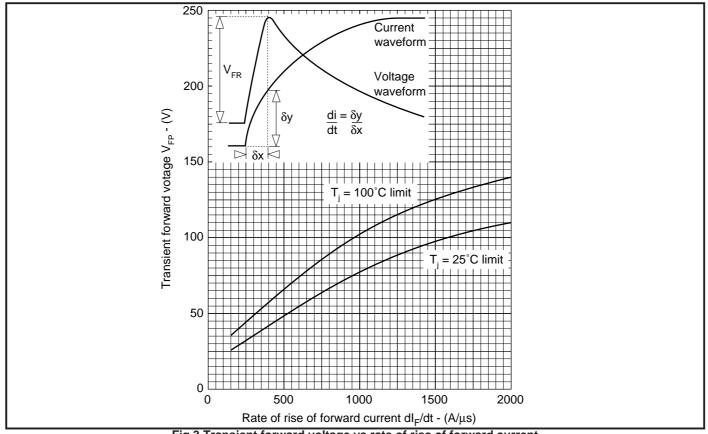


Fig.3 Transient forward voltage vs rate of rise of forward current

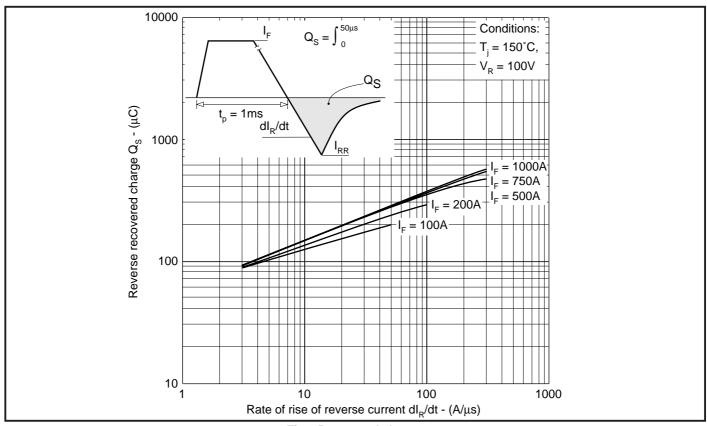


Fig.4 Recovered charge

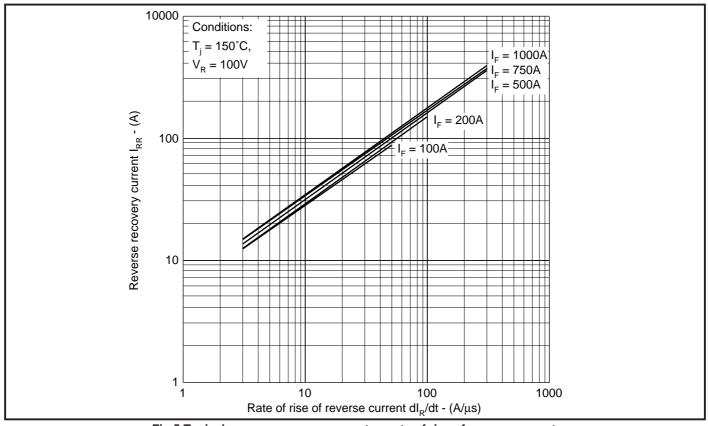


Fig.5 Typical reverse recovery current vs rate of rise of reverse current

# TV18..F

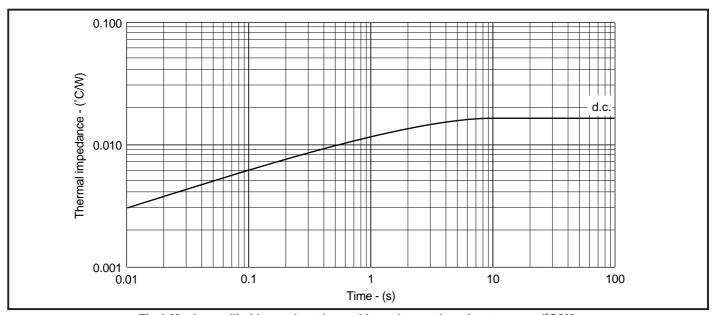
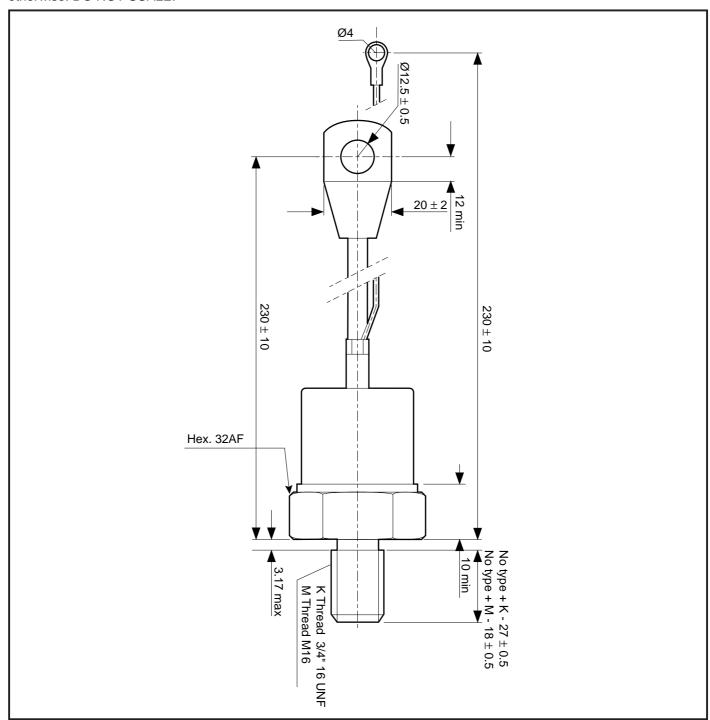


Fig.6 Maximum (limit) transient thermal impedance - junction to case - (°C/W)

### **PACKAGE DETAILS**

For further package information, please contact your local Customer Service Centre. All dimensions in mm, unless stated otherwise. DO NOT SCALE.



### **ASSOCIATED PUBLICATIONS**

Title	Application Note	
	Number	
Calculating the junction temperature or power semiconductors	AN4506	
Thyristor and diode measurement with a multi-meter	AN4853	
Use of V <sub>TO</sub> , r <sub>T</sub> on-state characteristic	AN5001	

#### TV18..F

#### POWER ASSEMBLY CAPABILITY

The Power Assembly group was set up to provide a support service for those customers requiring more than the basic semiconductor, and has developed a flexible range of heatsink / clamping systems in line with advances in device types and the voltage and current capability of our semiconductors.

We offer an extensive range of air and liquid cooled assemblies covering the full range of circuit designs in general use today. The Assembly group continues to offer high quality engineering support dedicated to designing new units to satisfy the growing needs of our customers.

Using the up to date CAD methods our team of design and applications engineers aim to provide the Power Assembly Complete solution (PACs).

#### **HEATSINKS**

Power Assembly has it's own proprietary range of extruded aluminium heatsinks. They have been designed to optimise the performance or our semiconductors. Data with respect to air natural, forced air and liquid cooling (with flow rates) is available on request.

For further information on device clamps, heatsinks and assemblies, please contact your nearest Sales Representative or the factory.



#### http://www.dynexsemi.com

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Preliminary Information: The product is in design and development. The datasheet represents the product as it is understood but details may change.

Advance Information: The product design is complete and final characterisation for volume production is well in hand.

No Annotation: The product parameters are fixed and the product is available to datasheet specification.

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